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Supporting information

Highly efficient and stable quantum dot light-emitting devices with low-temperature tin oxide electron transport layer

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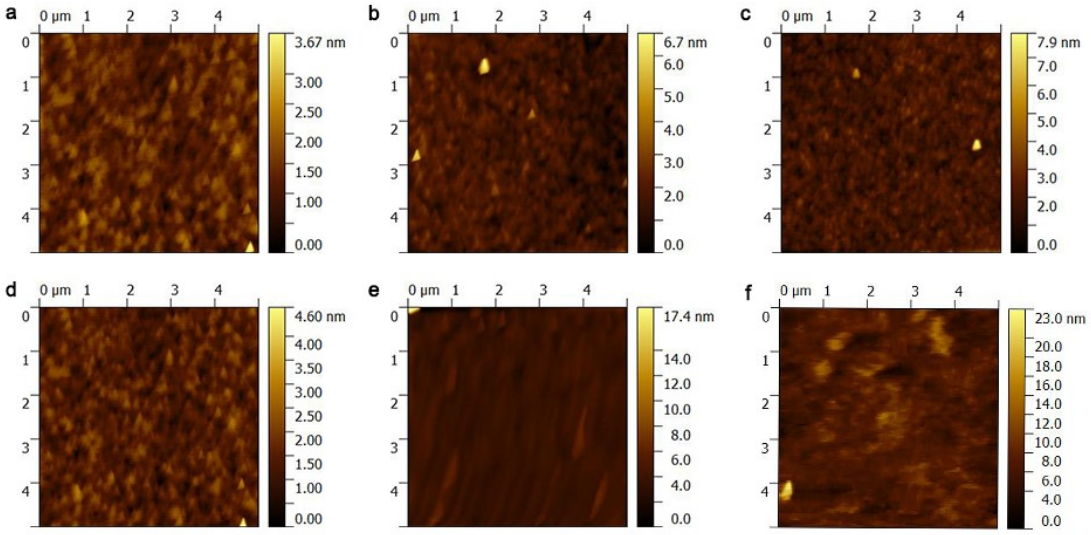

Figure S1 The surface morphology images of ITO/SnO_2 films under the annealing temperature of 120, 140, 160, 180, 200, 260 °C, respectively.

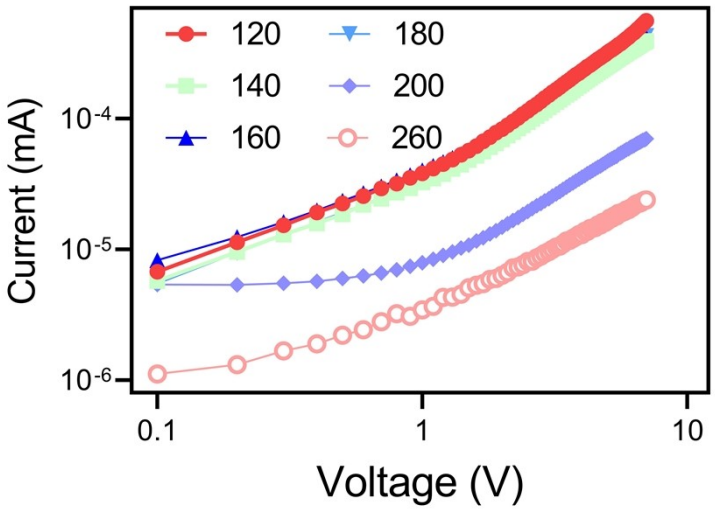

Figure S2 The lateral conductivity of ITO/SnO_2 film with the annealing temperature of 120, 140, 160, 180, 200, and 260 °C, respectively.

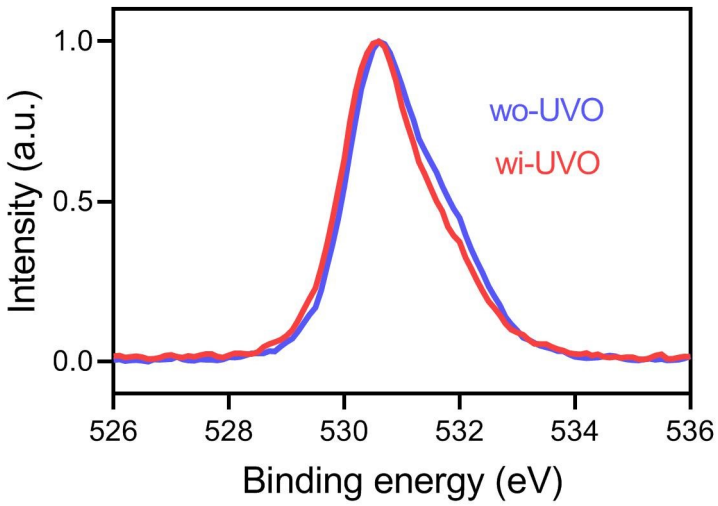

Figure S3 The combined figure of high-resolution O 1s spectra of wo-UVO and the wi-UVO films.